

SPECIFICATION

DEVICE NAME : Power MOSFET

TYPE NAME : 2SK2690-01

SPEC. NO. :

Fuji Electric Co.,Ltd.

This Specification is subject to change without notice.

	DATE	NAME	APPROVED	Fuji Electric Co.,Ltd.	
DRAWN				DWG. NO.	1/3
CHECKED					

- 1.Scope** This specifies Fuji Power MOSFET 2SK2690-01
- 2.Construction** N-Channel enhancement mode power MOSFET
- 3.Applications** for Switching
- 4.Outview** T0-3P Outview See to 5/13 page

5.Absolute Maximum Ratings at Tc=25°C (unless otherwise specified)

Description	Symbol	Characteristics	Unit	Remarks
Drain-Source Voltage	V _{DS}	60	V	
Continuous Drain Current	I _D	±80	A	
Pulsed Drain Current	I _{DP}	±320	A	
Gate-Source Voltage	V _{GS}	±20	V	
Maximum Avalanche Energy	E _{AV}	599	mJ	*1
Maximum Power Dissipation	P _D	125	W	
Operating and Storage	T _{ch}	150	°C	
Temperature range	T _{stg}	-55 to +150	°C	

*1 L=0.125mH, V_{CC}=24V

6.Electrical Characteristics at Tc=25°C (unless otherwise specified)

Static Ratings

Description	Symbol	Conditions	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =1mA V _{GS} =0V	60			V
Gate Threshold Voltage	V _{GS(th)}	I _D =1mA V _{DS} =V _{GS}	1.0	1.5	2.0	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V V _{GS} =0V		10	500	μA
		T _{ch} =25°C				
		T _{ch} =125°C		0.2	1.0	mA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =20V V _{DS} =0V		10	100	nA
Drain-Source On-State Resistance	R _{DS(on)}	I _D =40A		12	17	mΩ
		V _{GS} =4V V _{GS} =10V		7.5	10	

Dynamic Ratings

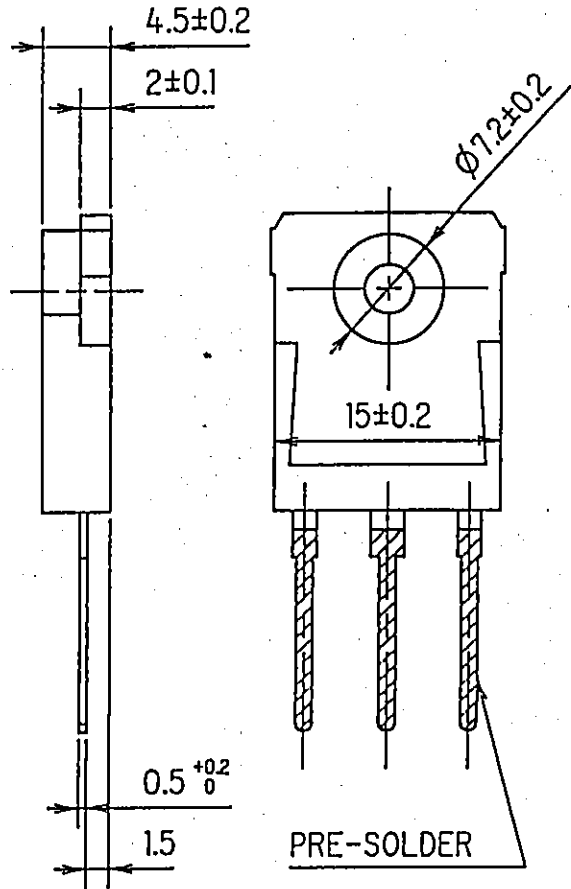
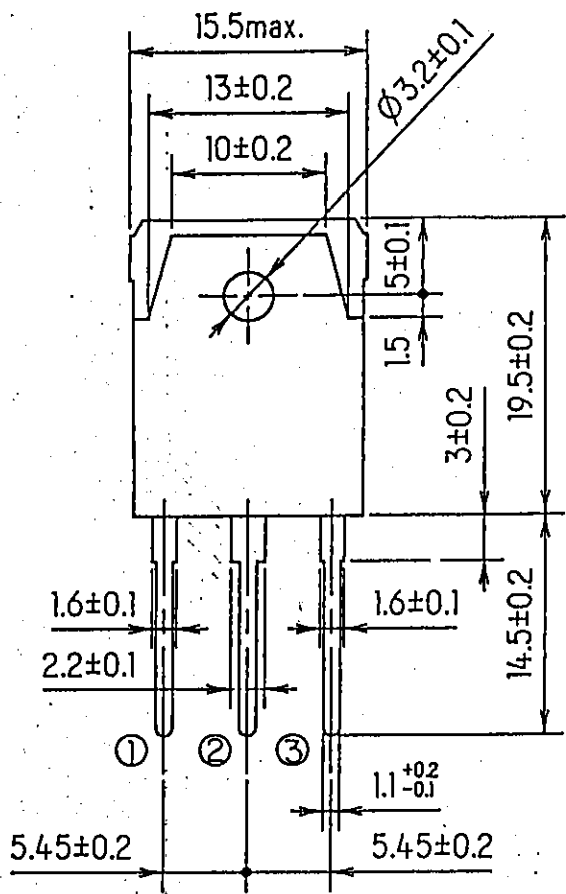
Description	Symbol	Conditions	min.	typ.	max.	Unit
Forward Transconductance	g_{fs}	$I_b=40A$ $V_{DS}=25V$	25	55		S
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1MHz$		3500	5250	pF
Output Capacitance	C_{oss}			1250	1870	
Reverse Transfer Capacitance	C_{rss}			360	540	
Turn-On Time	$t_{d(on)}$	$V_{ce}=30V$		15	23	ns
	t_r	$V_{GS}=10V$		75	120	
Turn-Off Time	$t_{d(off)}$	$I_b=75A$		190	285	
	t_f	$R_{GS}=10\Omega$		110	165	

Reverse Diode

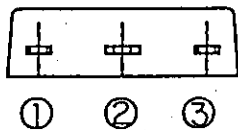
Description	Symbol	Conditions	min.	typ.	max.	Unit
Avalanche Capability	I_{AV}	$L=100\mu H$ $T_{ch}=25^\circ C$ See Fig.1 and Fig.2	80			A
Diode Forward On-Voltage	V_{SD}	$I_F=160A$ $V_{GS}=0V$ $T_{ch}=25^\circ C$		1.15	1.65	V
Reverse Recovery Time	t_{rr}	$I_F=80A$ $-di/dt=100A/\mu s$ $T_{ch}=25^\circ C$		75	120	ns
Reverse Recovery Charge	Q_{rr}				0.17	

7. Thermal Resistance

Description	Symbol	min.	typ.	max.	Unit
Channel to Case	$R_{th(ch-c)}$			1.00	$^\circ C/W$
Channel to Ambient	$R_{th(ch-a)}$			35.0	$^\circ C/W$



DIMENSIONS ARE IN MILLIMETERS.



CONNECTION

- ① GATE
- ② DRAIN
- ③ SOURCE

JEDEC : TO-228AA
EIAJ : SC-65
